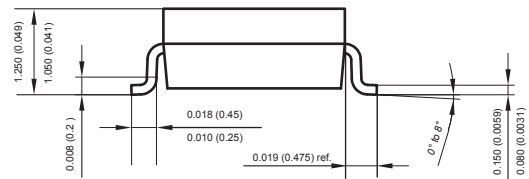
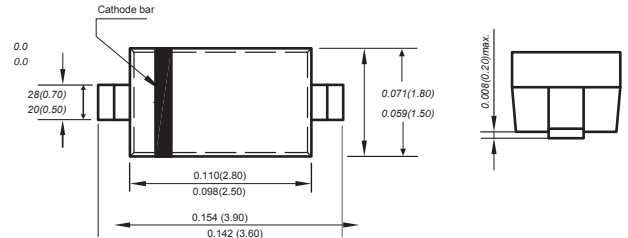


Features

- Metal silicon junction, majority carrier conduction
- Guarding for overvoltage protection
- Low power loss, high efficiency
- High current capability
- Low forward voltage drop
- High surge capability
- For use in low voltage, high frequency inverters, free wheeling, and polarity protection applications

Marking

NO.	1N5817W	1N5818W	1N5819W
Marking	SJ	SK	SL



Dimensions in inches and (millimeters)

Absolute Maximum Ratings (Ta=25°C unless otherwise specified)

Parameter	Symbols	1N5817WS	1N5818WS	1N5819WS	Units
Maximum Repetitive Peak Reverse Voltage	V_{RRM}	20	30	40	V
Maximum RMS voltage	V_{RMS}	14	21	28	V
Maximum DC Blocking Voltage	V_{DC}	20	30	40	V
Maximum Average Forward Rectified Current	$I_{F(AV)}$	1			A
Peak Forward Surge Current, 8.3ms Single Half Sine-wave Superimposed On Rated Load (JEDEC)	I_{FSM}	9			A
Maximum Instantaneous Forward Voltage at 1 A at 3 A	V_F	0.45 0.75	0.55 0.875	0.6 0.9	V
Maximum Instantaneous Reverse Current at $T_A = 25^\circ\text{C}$ Rated DC Reverse Voltage $T_A = 100^\circ\text{C}$	I_R	1 10			mA
Typical Junction Capacitance	C_J	110			pF
Storage and Operating Junction Temperature Range	T_J, T_{stg}	-55 ~ +150			°C



Typical Characteristic Curves

Fig.1 Forward Current Derating Curve

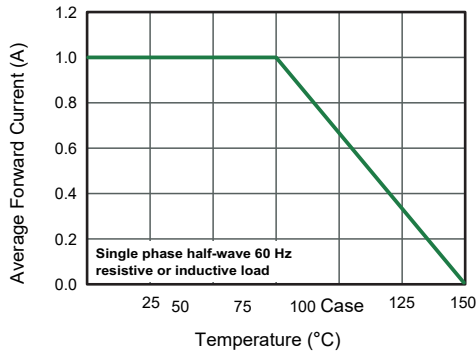


Fig.2 Typical Reverse Characteristics

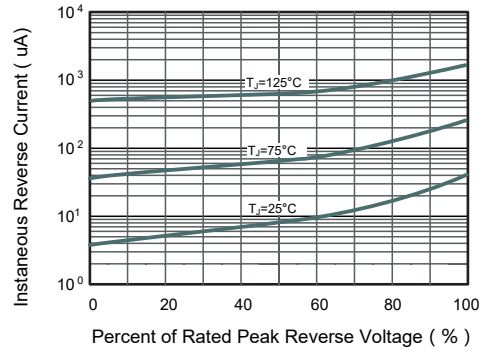


Fig.3 Typical Forward Characteristic

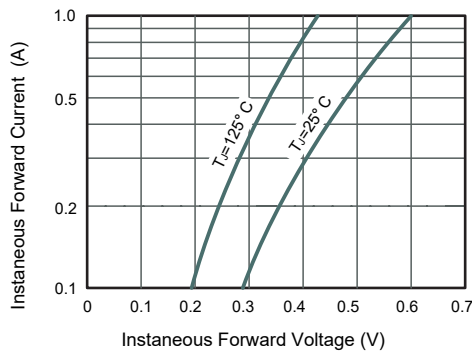
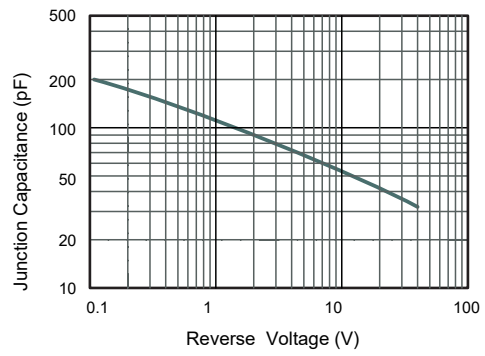
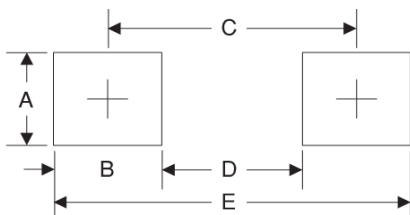


Fig.4 Typical Junction Capacitance



Suggested Pad Layout



Symbol	Unit (mm)	Unit (inch)
A	1.2	0.047
B	1.2	0.047
C	3.2	0.126
D	2	0.079
E	4.4	0.173